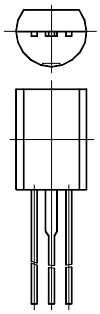
Transys Electronics LIMITED

TO-92MOD Plastic-Encapsulated Transistors

2SB892 TRANSISTOR (PNP)

TO-92MOD

1. EMITTER
2. COLLECTOR
3. BASE



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FEATURE

Power dissipation

P_{CM}: 1 W (Tamb=25℃)

Collector current

I_{CM}: -2 A

Collector-base voltage

$V_{(BR)CBO}$: -60 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= -10μA , I_E=0	-60		V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= -1mA , I_B=0	-50		V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E=- 100μA, I_C=0	-6		V
Collector cut-off current	I_{CBO}	V_{CB}= -50V , I_E=0		-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -4V , I_C=0		-0.1	μA
DC current gain	$H_{FE(1)}$	V_{CE}=-2V, I_C= -100mA	100	560	
	$H_{FE(2)}$	V_{CE}=-2V, I_C= -1.5A	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= -1A, I_B= -50mA		-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C= -1A, I_B= -50mA		-1.2	V
Transition frequency	f_T	V_{CE}= -10 V, I_C= -50mA	150		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	S	T	U
Range	100-200	140-280	200-400	280-560